

Supplementary Material:

Continuous wave mid-infrared lasing from single InAs nanowires grown on silicon

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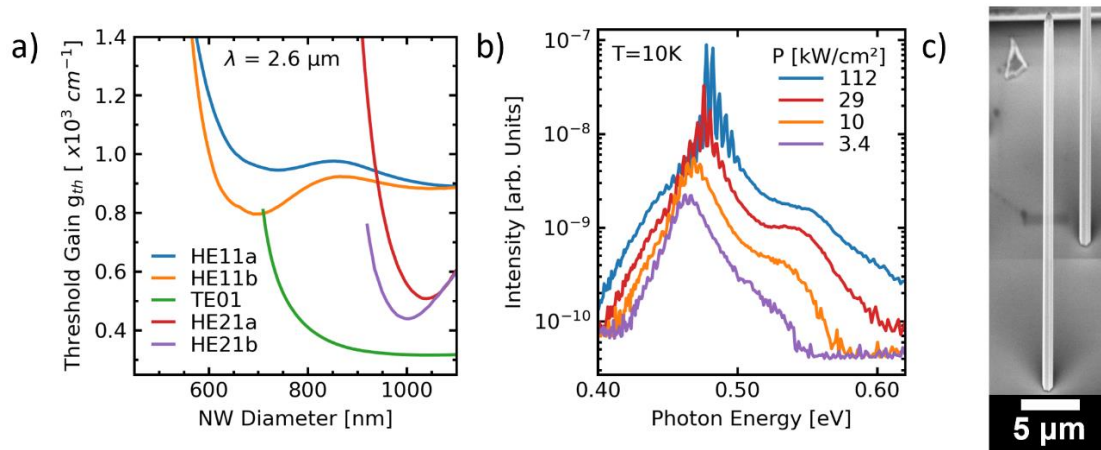


Figure 1 (a) FDTD simulations of the threshold gain for different guided modes, (b) Power dependent micro-PL spectra recorded from an individual InAs nanowire laser (c) SEM image of as grown InAs nanowires on silicon